

Data Sheet January 2002

30A, 400V - 600V Hyperfast Diodes

The RHRG3040 and RHRG3060 are hyperfast diodes with soft recovery characteristics (t_{rr} < 40ns). They have half the recovery time of ultrafast diodes and are of silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/ clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Formerly developmental type TA49063.

Ordering Information

PART NUMBER	PACKAGE	BRAND		
RHRG3040	TO-247	RHRG3040		
RHRG3060	TO-247	RHRG3060		

NOTE: When ordering, use the entire part number.

Symbol



Features

•	Hyperfast with Soft Recovery<40ns
•	Operating Temperature
•	Reverse Voltage Up To

- Avalanche Energy Rated
- Planar Construction

Applications

- · Switching Power Supplies
- · Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE TO-247



Absolute Maximum Ratings T_C = 25°C, Unless Otherwise Specified

	RHRG3040	RHRG3060	UNITS	
Peak Repetitive Reverse Voltage	400	600	V	
Working Peak Reverse Voltage	400	600	V	
DC Blocking VoltageV _F	R 400	600	V	
Average Rectified Forward Current $I_{F(AV)}$ ($T_{C} = 120^{\circ}C$)) 30	30	A	
Repetitive Peak Surge CurrentIFRN (Square Wave, 20kHz)	70	70	Α	
Nonrepetitive Peak Surge Current	325	325	Α	
Maximum Power Dissipation	125	125	W	
Avalanche Energy (See Figures 10 and 11)	_ 20	20	mJ	
Operating and Storage Temperature	-65 to 175	-65 to 175	°C	

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Electrical Specifications T_C = 25°C, Unless Otherwise Specified

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	WY.CON.TY WY	RHRG3040		RHRG3060			-31	
SYMBOL	TEST CONDITION	MIN	ТҮР	MAX	MIN	TYP	MAX	UNITS
V _F	I _F = 30A	- 1N.10	07.	2.1	- 11	WW.10	2.1	V
	$I_F = 30A, T_C = 150^{\circ}C$	-	007	1.7	- 1	- N-W.1	1.7	V
IR	V _R = 400V	MAIN	1007	250	<u>-</u>	W Tan W	1005.	μА
	V _R = 600V	N	N.100X.	TIMOS		N T	250	μА
	V _R = 400V, T _C = 150°C	1 In	W.1907.	1.0	-	N. T.	W. 700x.	mA
	$V_R = 600V, T_C = 150^{\circ}C$	7//	100°	MOD	III-	- IN A	1.0	mA
t _{rr}	$I_F = 1A$, $dI_F/dt = 200A/\mu s$	- 11	100	40	LTY	- 11	40	ns
	$I_F = 30A$, $dI_F/dt = 200A/\mu s$	- 1	1.VI	45	M.T.W	- 11	45	ns
ta	$I_F = 30A$, $dI_F/dt = 200A/\mu s$	-	22	007	MIN	22	- W.1	ns
t _b	$I_F = 30A$, $dI_F/dt = 200A/\mu s$	-	18	1007.	ONETV	18	W T	ns
Q _{RR}	$I_F = 30A$, $dI_F/dt = 200A/\mu s$	N -	100	N.10-0X.	T.MO	100	-	nC
CJ	V _R = 10V, I _F = 0A	[] -	85	W.1-00X	COM.	85	N. A.	pF
$R_{\theta JC}$	MM 100X.Com	TW	-11/1/	1.2	Mos	IN	1.2	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time (See Figure 9), summation of t_a + t_b.

ta = Time to reach peak reverse current (See Figure 9).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

Q_{RR} = Reverse recovery charge.

C_J = Junction Capacitance.

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

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Typical Performance Curves

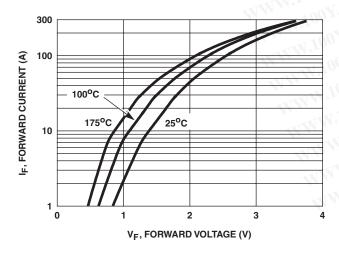


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

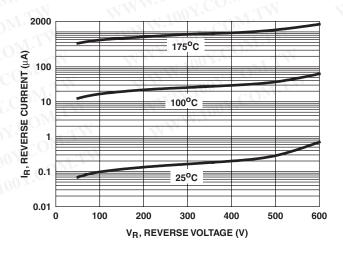


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

100

Typical Performance Curves (Continued)

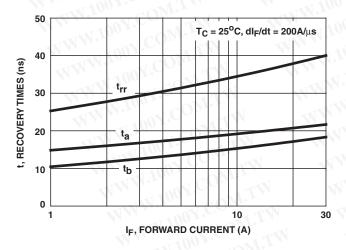
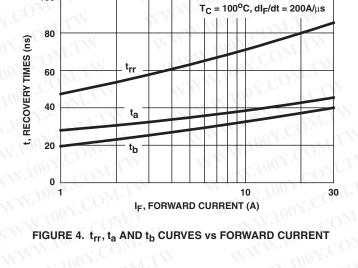


FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT



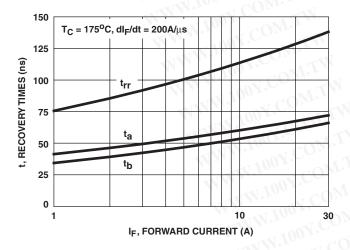


FIGURE 5. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

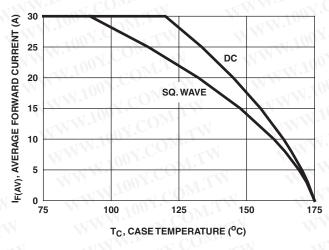


FIGURE 6. CURRENT DERATING CURVE

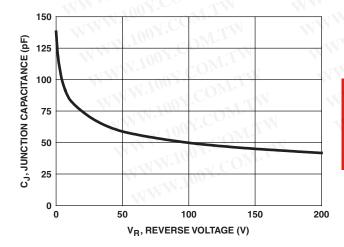


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

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Test Circuits and Waveforms

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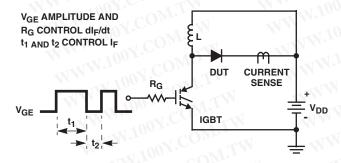


FIGURE 8. t_{rr} TEST CIRCUIT

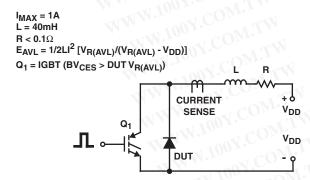


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

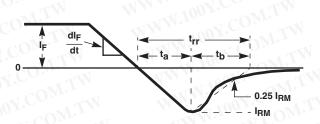


FIGURE 9. t_{rr} WAVEFORMS AND DEFINITIONS

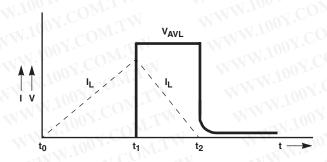


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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